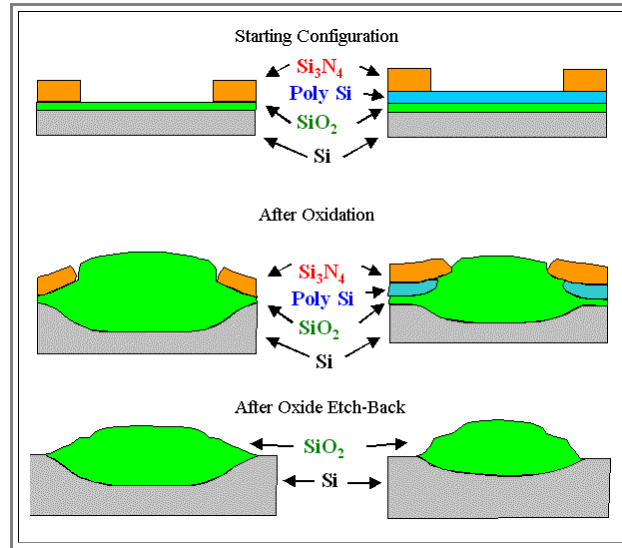


LOCOS with Sacrificial Poly-Silicon

Illustration

Here is a comparison of the [LOCOS process](#) with and without some sacrificial poly-Si:



● Provided, some of the oxide is removed by an "etch-back" process, the lateral extension can be kept somewhat smaller than in the conventional case.

While this makes things quite complicated, the final versions of the **LOCOS** process were even more complicated.